Supporting information for the manuscript Bi₂Se₃-PtSe₂ heterostructure ultrabroadband UV-to-THz negative photoconductive photodetectors with wide-temperature-range operation

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Figure S2. Plot of photocurrent versus optical power density for Bi₂Se₃-PtSe₂ heterojunction photodetector under 405-1550 nm band illumination.



Figure S3. Stability testing of Bi_2Se_3 -PtSe₂ heterojunction photodetectors under 405-808 nm illumination.



Figure S4. Optical power versus current in Bi_2Se_3 -PtSe₂ heterojunction photodetectors under 405-808 nm illumination.



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Figure S6. Performance comparison of different Bi₂Se₃-PtSe₂ heterojunction photodetectors under the same test conditions.